L Number	Hits	Search Text	DB	Time stamp
1	930	438/14 .CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/03 13:44
-	2	("5940704").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 14:14
-	0	5940704.URPN.	USPAT;	2001/12/31 13:04
-	1821	second and transistor and reference adj voltage and measuring and testing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 13:06
-	37	measuring adj current near drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 13:29
-	0	reticle adj option adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 13:13
-	37196	wafer and test	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 13:32
-	17233	reticle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 13:15
-	1638	(wafer and test) and reticle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 13:16
-	13608	(probe or probing) and die	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 13:16
-	123	((wafer and test) and reticle) and ((probe or probing) and die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 13:17
-	891341	pin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 13:17
-	5333	test adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 14:20
-	0	((((wafer and test) and reticle) and (probe or probing) and die)) and pin) and (test adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/31 13:18

-	57	.. wafer and test; and reticle; and ((probe or probing; and die)' and pin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:28
-	7514	"burn-in"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:28
-	1997	(wafer and test) and "burn-in"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 14:13
-	695	((probe or probing) and die) and ((wafer and test) and "burn-in")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:28
-	462	pin and (((probe or probing) and die) and ((wafer and test) and "burn-in"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:28
-	11376	measuring adj current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:29
-	8	(pin and (((probe or probing) and die) and ((wafer and test) and "burn-in"))) and (measuring adj current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:31
-	133141	reference adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:32
-	152	(wafer and test) and "burn-in" and (reference adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:32
-	153889	source and gate and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:33
-	88	((wafer and test) and "burn-in" and (reference adj voltage)) and (source and gate and drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:47
-	6	(measuring adj current) and (((wafer and test) and "burn-in" and (reference adj voltage)) and (source and gate and drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 13:47
-	2	("4758863").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 14:14
-	18	4758863.URPN.	USPAT	2002/12/31 14:14
-	1	test adj voltage and 4758863.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 14:21

-	51233	process adj control	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 14:22
-	27	(wafer and test) and "burn-in" and (process adj control)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 14:23